



FGH30N60LSD

Features

- Low saturation voltage: $V_{CE(sat)} = 1.1V @ I_C = 30A$
- High Input Impedance
- Low Conduction Loss

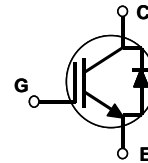
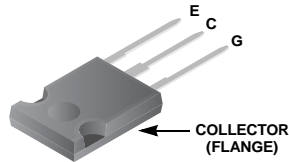
Applications

- Solar Inverters
- UPS, Welder



General Description

The FGH30N60LSD is a MOS gated high voltage switching device combining the best features of MOSFETs and bipolar transistors. This device has the high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor.



Absolute Maximum Ratings

Symbol	Description	FGH30N60LSD	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ C$	60	A
	Collector Current @ $T_C = 100^\circ C$	30	A
$I_{CM(1)}$	Pulsed Collector Current	90	A
I_{FSM}	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	150	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ C$	480	W
	Maximum Power Dissipation @ $T_C = 100^\circ C$	192	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ C$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ C$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case	--	0.26	$^\circ C/W$
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction-to-Case	--	0.92	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ C/W$

Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGH30N60LSD	FGH30N60LSDTU	TO-247	Tube	30ea	-

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
V_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\frac{\Delta V_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 250	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\mu A, V_{CE} = V_{GE}$	4.0	5.5	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 30A, V_{GE} = 15V$	--	1.1	1.4	V
		$I_C = 30A, V_{GE} = 15V, T_C = 125^\circ C$	--	1.0	--	V
		$I_C = 60A, V_{GE} = 15V$	--	1.3	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V, f = 1MHz$	--	3550	--	pF
C_{oes}	Output Capacitance		--	245	--	pF
C_{res}	Reverse Transfer Capacitance		--	90	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400V, I_C = 30A, R_G = 6.8\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 25^\circ C$	--	18	--	ns
t_r	Rise Time		--	46	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	250	--	ns
t_f	Fall Time		--	1.3	2.0	μs
E_{on}	Turn-On Switching Loss		--	1.1	--	mJ
E_{off}	Turn-Off Switching Loss		--	21	--	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400V, I_C = 30A, R_G = 6.8\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 125^\circ C$	--	17	--	ns
t_r	Rise Time		--	45	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	270	--	ns
t_f	Fall Time		--	2.6	--	μs
E_{on}	Turn-On Switching Loss		--	1.1	--	mJ
E_{off}	Turn-Off Switching Loss		--	36	--	mJ
Q_g	Total Gate Charge	$V_{CE} = 300V, I_C = 30A, V_{GE} = 15V$	--	225	--	nC
Q_{ge}	Gate-Emitter Charge		--	30	--	nC
Q_{gc}	Gate-Collector Charge		--	105	--	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	7	--	nH

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Conditions	Min.	Typ.	Max	Units	
V_{FM}	$I_F = 15\text{A}$	$T_C = 25^\circ\text{C}$	-	1.8	2.2	V
	$I_F = 15\text{A}$	$T_C = 125^\circ\text{C}$	-	1.6	-	V
I_{RM}	$V_R = 600\text{V}$	$T_C = 25^\circ\text{C}$	-	-	100	μA
t_{rr}	$I_F = 1\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$, $V_{CC} = 30\text{V}$	$T_C = 25^\circ\text{C}$	-	-	35	ns
	$I_F = 15\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$, $V_{CC} = 390\text{V}$	$T_C = 25^\circ\text{C}$	-	-	40	ns
t_a	$I_F = 15\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$, $V_{CC} = 390\text{V}$	$T_C = 25^\circ\text{C}$	-	18	-	ns
t_b		$T_C = 25^\circ\text{C}$	-	13	-	ns
Q_{rr}		$T_C = 25^\circ\text{C}$	-	27.5	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

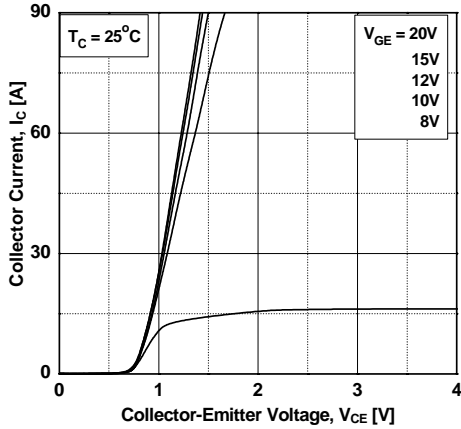


Figure 2. Typical Saturation Voltage Characteristics

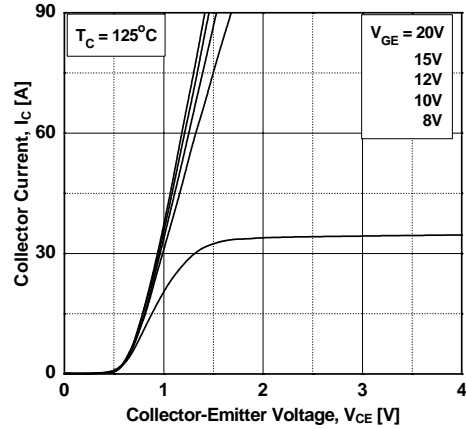


Figure 3. Typical Saturation Voltage Characteristics

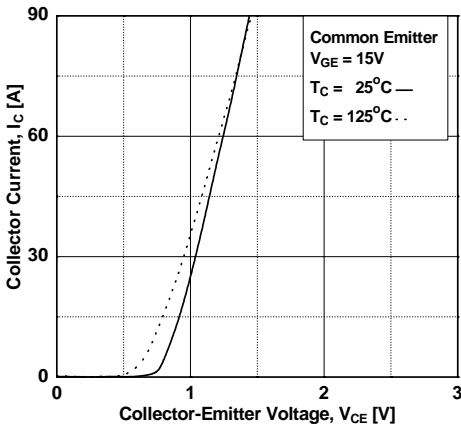


Figure 4. Transfer characteristics

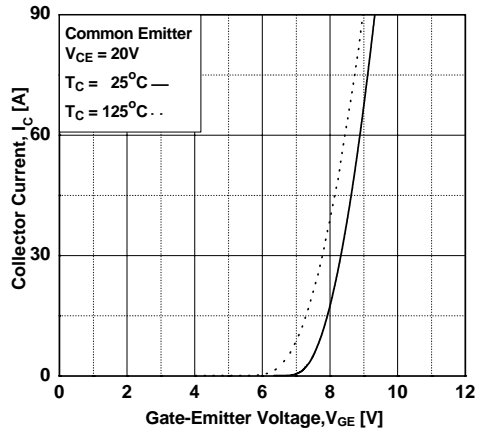


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

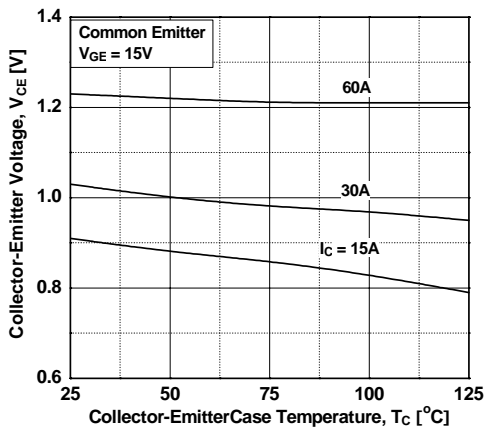
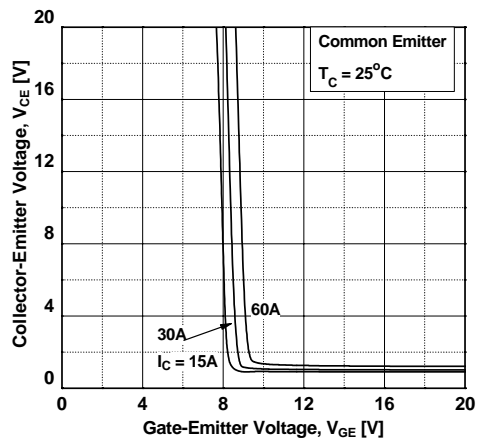


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage vs. V_{GE}

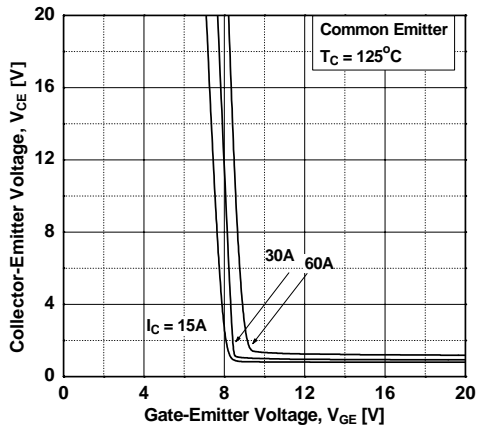


Figure 8. Capacitance characteristics

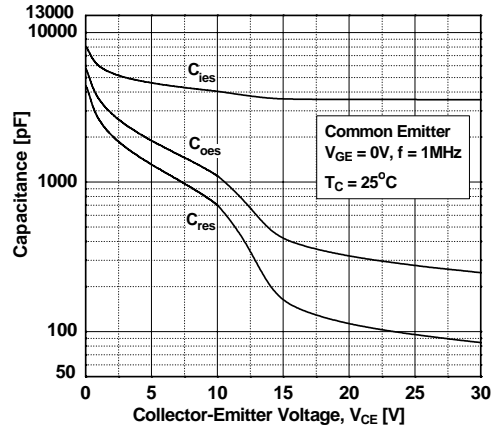


Figure 9. Gate Charge Characteristics

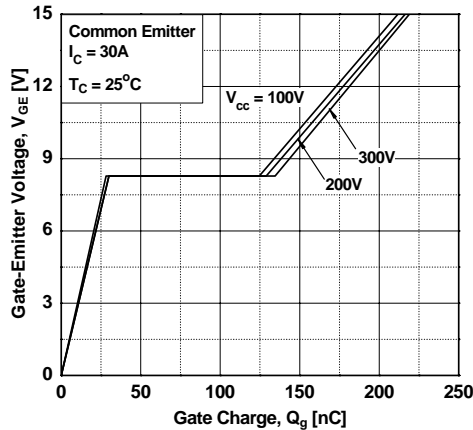


Figure 10. SOA Characteristics

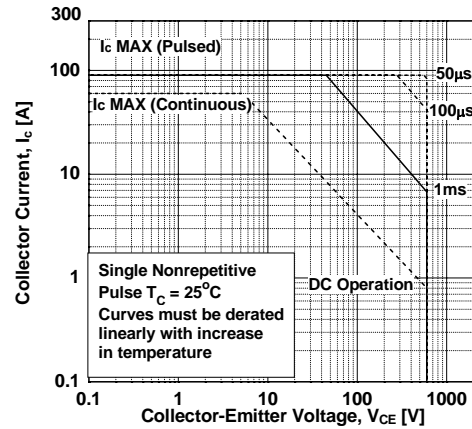


Figure 11. Load Current Vs. Frequency

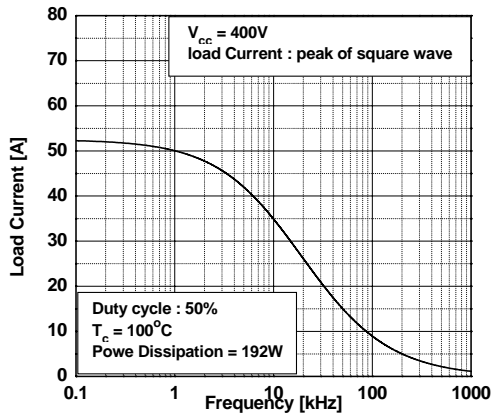
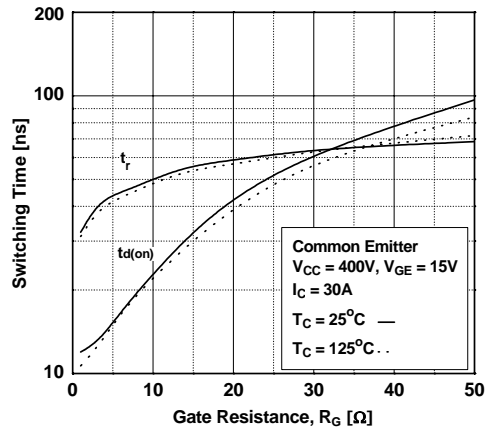


Figure 12. Turn-On Characteristics vs. Gate Resistance



Typical Performance Characteristics (Continued)

Figure 13. Turn-Off Characteristics vs. Gate Resistance

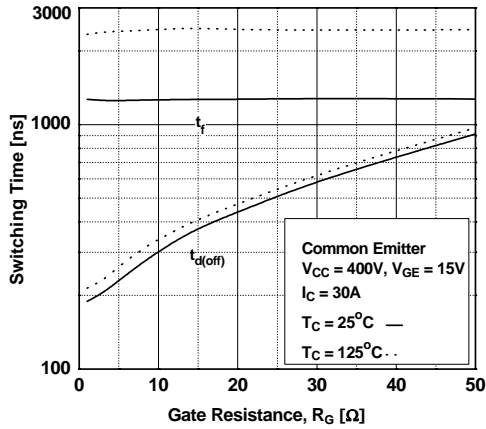


Figure 15. Turn-Off Characteristics vs. Collector Current

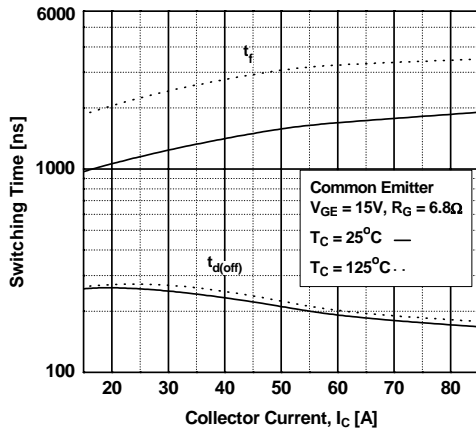


Figure 17. Switching Loss vs Collector Current

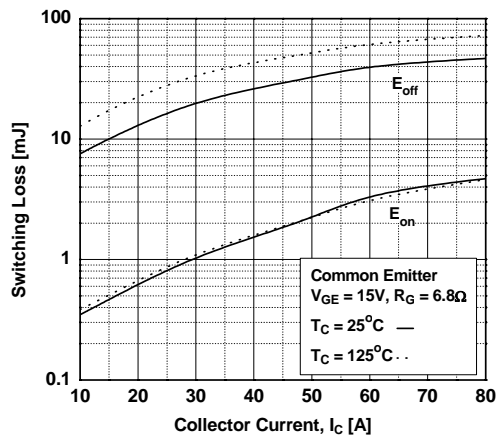


Figure 14. Turn-On Characteristics vs. Collector Current

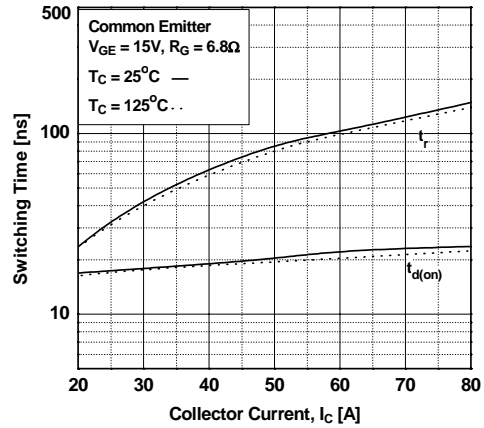


Figure 16. Switching Loss vs Gate Resistance

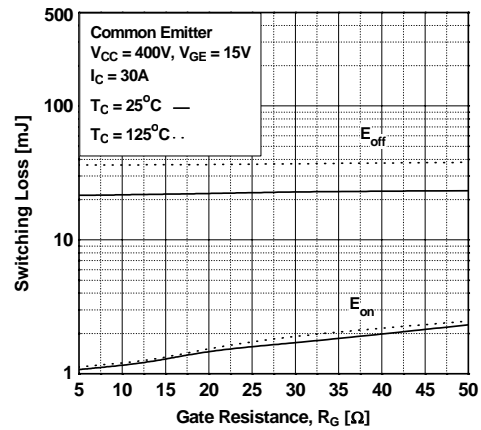


Figure 18. Turn-Off Switching SOA Characteristics

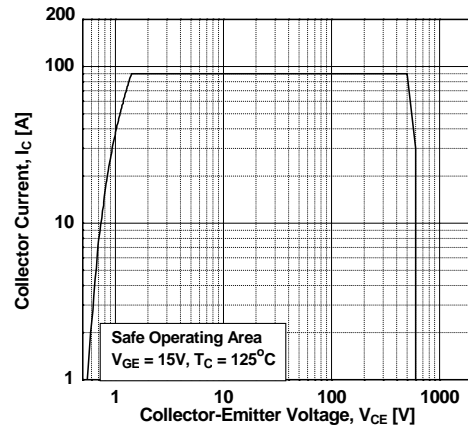


Figure 19. Transient Thermal Impedance of IGBT

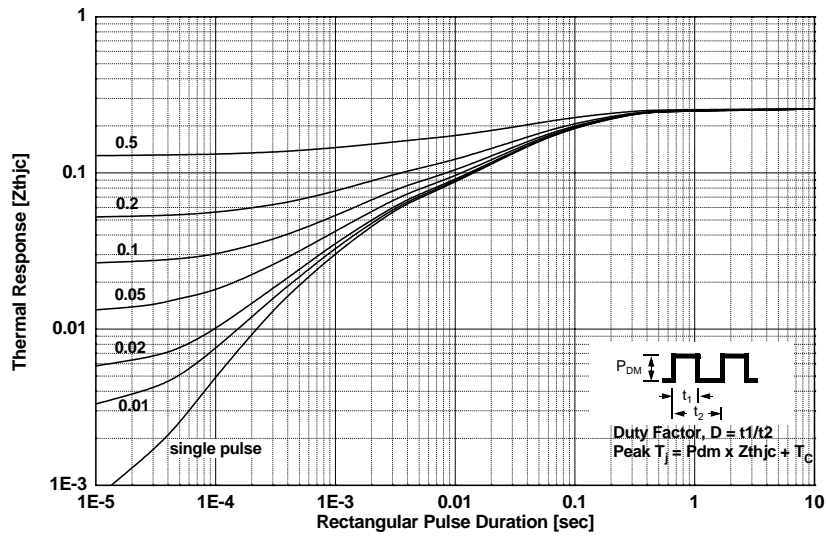


Figure 20. Typical Forward Voltage Drop

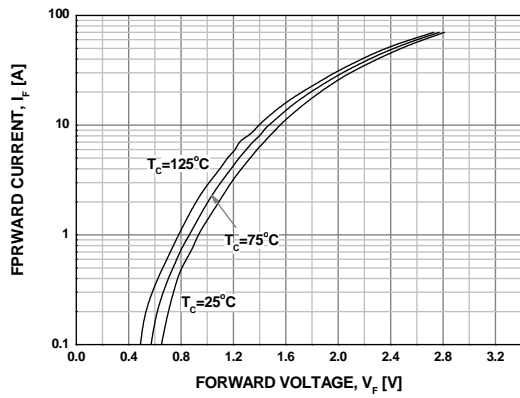


Figure 21. Typical Reverse Current

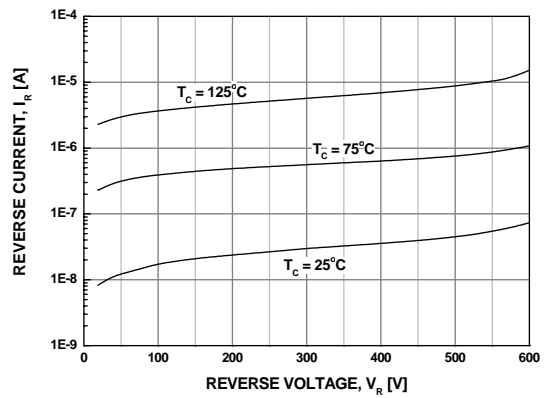
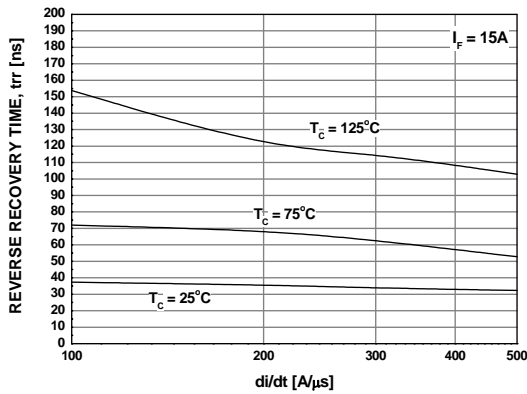
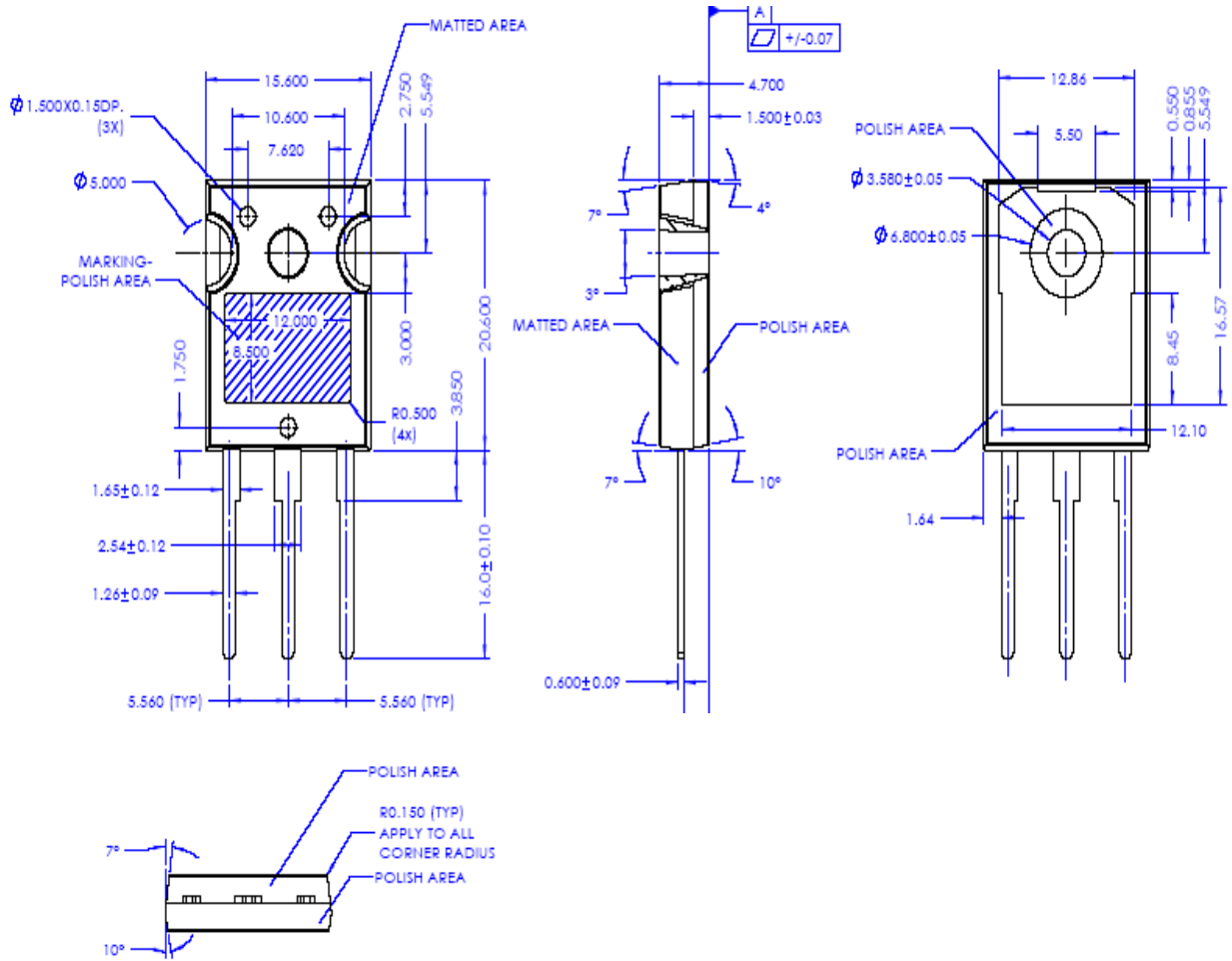


Figure 22. Typical Reverse Recovery Time



Mechanical Dimensions TO-247AB (FKS PKG CODE 001)



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